TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

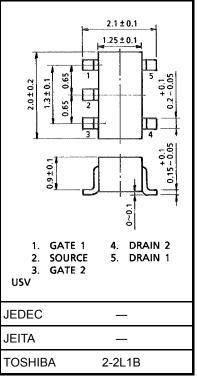
SSM5N05FU

High Speed Switching Applications

- Optimum for high-density mounting in small packages
- Low on-resistance: $R_{on} = 0.8 \Omega (max) (@V_{GS} = 4 V)$: $R_{on} = 1.2 \Omega (max) (@V_{GS} = 2.5 V)$
- Low gate threshold voltage

Absolute Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristics		Symbol	Rating	Unit	
Drain-Source voltage		V _{DS}	20	V	
Gate-Source voltage		V _{GSS}	±12	V	
Drain current	DC	۱ _D	400	mA	
	Pulse	I _{DP}	800		
Drain power dissipation (Ta = 25° C)		P _D (Note 1)	300	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



Weight: 6 mg (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e.

> operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook

("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Total rating, mounted on FR4 board (25.4 mm \times 25.4 mm \times 1.6 t, Cu Pad: 0.32 mm² \times 5)

Handling Precaution

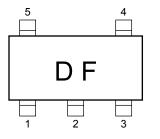
When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

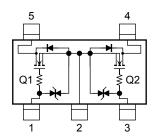
Unit: mm

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Marking

Equivalent Circuit (top view)





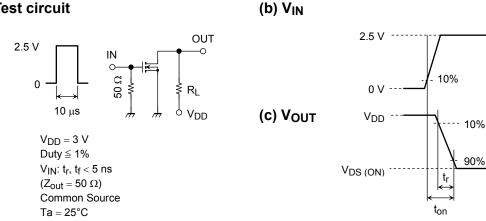
Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS}=\pm 12~V,~V_{DS}=0$	_	_	±1	μA
Drain-Source breakdown voltage		V (BR) DSS	$I_D = 1 \text{ mA}, V_{GS} = 0$	20	_	_	V
Drain cut-off current		I _{DSS}	$V_{DS} = 20 \text{ V}, V_{GS} = 0$	_	_	1	μA
Gate threshold voltage	9	V _{th}	$V_{DS} = 3 \text{ V}, \text{ I}_{D} = 0.1 \text{ mA}$	0.6	_	1.1	V
Forward transfer admittance		Y _{fs}	$V_{DS} = 3 \text{ V}, \text{ I}_{D} = 200 \text{ mA} \qquad (\text{Note2})$	350	_	_	mS
Drain-Source on-resistance		R _{DS (ON)}	$I_D = 200 \text{ mA}, V_{GS} = 4 \text{ V} \qquad (\text{Note2})$	_	0.6	0.8	Ω
			$I_D = 200 \text{ mA}, V_{GS} = 2.5 \text{ V}$ (Note2)		0.85	1.2	
Input capacitance		C _{iss}			22		pF
Reverse transfer capacitance		C _{rss}	$V_{DS} = 3 V$, $V_{GS} = 0$, f = 1 MHz		9		pF
Output capacitance		Coss			21		pF
Switching time	Turn-on time	t _{on}	$V_{DD} = 3 V, I_D = 100 mA,$		60		ns
	Turn-off time	t _{off}	V _{GS} = 0~2.5 V	_	70		

Note2: Pulse test

Switching Time Test Circuit

(a) Test circuit



Precaution

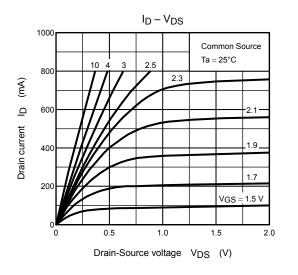
 V_{th} can be expressed as the voltage between gate and source when the low operating current value is $I_D = 100 \ \mu A$ for this product. For normal switching operation, V_{GS} (on) requires a higher voltage than V_{th} and V_{GS} (off) requires a lower voltage than V_{th} . (The relationship can be established as follows: V_{GS} (off) < V_{th} < V_{GS} (on))

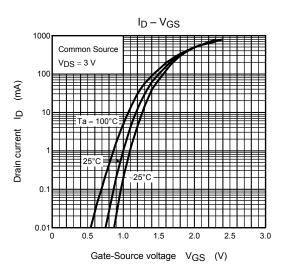
Please take this into consideration when using the device.

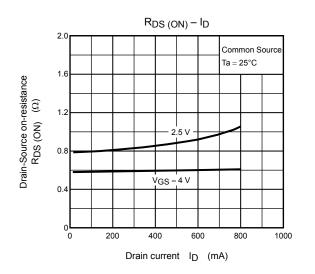
90%

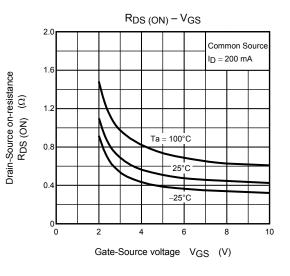
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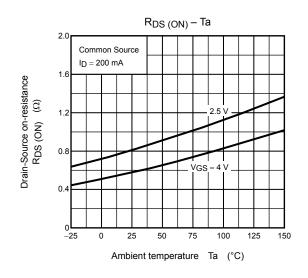
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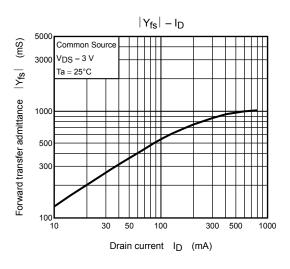






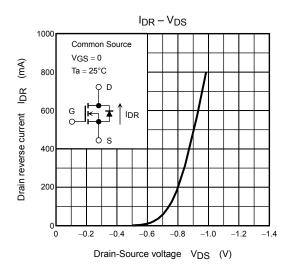


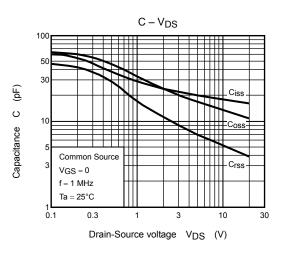


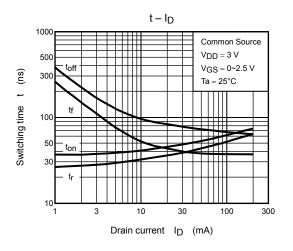


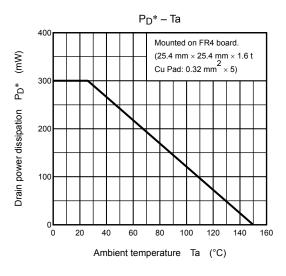
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(Q1, Q2 common)









*: Total rating

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20070701-EN GENERAL

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